trom 9.00 Company registration opens	Program DGKK Workshop 2017						
1930 Regular registration opens Light funch available for all, Foyer Aula 1946 Opening of the workshop and company exhibition Regular Registration of personal company exhibition 1950 Maine Title Regular Registration Regular Re	Thursday, 07.12.2017						
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Session 2a: Patterned Substrates & Selected Area Growth 16:30 S. Walde			Growth of AIN by pulsed reactive magnetron sputter deposition	L. Grieger	Fully automated measurement and analysis of reciprocal space maps		
Session 2a: Patterned Substrates & Selected Area Growth 16:30 S. Walde All growth on nano-patterned sapphire substrates Low Threading discostion density All/sapphire templates by high temperature annealing. Site controlled MCVPE of Galv nanorods by governing the Local Polarity of All on Sitt 11). 17:10 C. Blumberg of All on Sitt 11). Provided of Schmidt microstructure with nonpolar sidewalls. 17:15 G. Schmidt microstructure with nonpolar sidewalls. 17:15 G. Schmidt microstructure with nonpolar sidewalls. 17:30 E. Gini cascade lasers. 17:30 E. Gini Sagnaskiy. 19:00 End 00:00 Times Name Title Name Title Name Title Name Title Correlation of structural and optical properties of GalviAin quantum disks generated and in anowires grown by MBE using highly spatially cathodoluminescence microscopy. 10:03 B. Sheng Correlation of structural and optical properties of GalviAin quantum disks growth of England on Structure annealing. 10:15 H. Zhou structures Session 3a: 3D Growth II Correlation of structural and optical properties of GalviAin quantum disks integrated by MBE-grown using highly spatially cathodoluminescence microscopy. M. Nandy In-situ study of AlxGa1-xP nucleation on As-modified Sit (100) 2° surfa R. Bek Direct orange emission from a semiconductor membrane laser. 10:15 H. Zhou structures Session 4a: Arsenides Session 4b: Nitrides Session 4b: Nitrides A Fariza Comparison of G-and Fe-doped Galv biffer layers and HEMT struct. A Fariza Comparison of G-and Fe-doped Galv biffer layers and HEMT struct.	5:15-16:30						
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17:00 C. Blumberg Direct comparison of structural and optical properties of GaN fin LED Direct comparison of structural and optical properties of GaN fin LED Direct comparison of structure with nonpolar sidewalls 17:30 E. Gini current blocking layers in buried heterostructure quantum Cascade lasers Single-photon sources based on site-controlled quantum dots with a record-high extraction efficiency Dinner "Historisches Kaufhaus" (cortool of unintentional oxygen incorporation in GaN End 00:00 Friday, 08. 12.2017 Room: Aula (ground floor) Time Name Title 9:00 B. Kunert Invited talk: Selective area growth of IIIIV on (001) Si Session 3a: 3D Growth II Correlation of structural and optical properties of GaN/AIN quantum disks embedded in nanowires grown by MBE using highly spatially cathodoluminescence microscopy 10:30 H. Schürmann 10:45-11:30 Coffee Break and Company Exhibition (sponsored by DOCKWEILER CHEMICALS), Foyer Aula and Foyer Forum III MN Agar Tin-assisted MBE-growth of c-Ga2O3 F. Schubert Control of unintentional oxygen incorporation in GaN 22:2017 Room: Forum III (third floor) Name Title Session 3b: Phosphides Correlation of structural and optical properties of GaN/AIN quantum disks embedded in nanowires grown by MBE using highly spatially cathodoluminescence microscopy 10:30 H. Schürmann 10:45-11:30 Coffee Break and Company Exhibition (sponsored by DOCKWEILER CHEMICALS), Foyer Aula and Foyer Forum III Session 4b: Nitrides J. Shahbaz InGaN Heterostructures as Gas Sensors MOVPE grown InGaAs Metamorphic Buffer layers and HEMT struct Transition metal doping in MBE-grown InGaAs: Ultrafast THz emitters			, ,		Influence of MOVPE Reactor Pressure and Temperature on the Nucleation and Lateral Growth		
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12:15 R. Lang Homogeneity and Minority Carrier Diffusion Length S. Neugebauer MOVPE of GaN tunnel junctions for large area InGaN LEDs	12:15 B La	ang	Homogeneity and Minority Carrier Diffusion Length	S. Neugebauer	MOVPE of GaN tunnel junctions for large area InGaN LEDs		
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12:30 A. Paszuk CVD ambient P. Horenburg Microscopic interface and composition analysis of lattice-matched All		aszuk			Microscopic interface and composition analysis of lattice-matched AllnN		
				M. Heuken	MOCVD Reactor Development for Cost Effective Micro LED Display Processing		
13:00 Closing Remarks of the Workshop	13:00						
Lunch (sponsored by OSRAM), Foyer Aula; from 13:30 Taxis leave for Tour at Fraunhofer ISE				yer Aula; from 13:30 T	axis leave for Tour at Fraunhofer ISE		
14:00-15:00 Guided Tour at Fraunhofer ISE							